

EAST: [10612913 protruded FOX.wsp:1]

File View Edit Tools Window Help

Active

L1: ((FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) a

L2: (38) (((lithograph\$6 optical\$2) near2 limit) sub-lithograph\$6)

Failed

Saved

(5838) bird\$3 adj beak

(8560395) (open\$5 hole aperture trench\$4 groove cavity concave convex depressor

(1804204) (curv\$4 contour\$4 arc concave convex)

(6425012) (open\$5 hole aperture trench\$4 groove cavity depression)

(532241) (FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) a

(44746) ((FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) ad

(2414) ((curv\$4 contour\$4 arc concave convex)0

(305) ((FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) adj2

(64931) ((float\$4 adj (gate electrode plate trap\$4) FG) charge adj storage )

(1565881) flat planar

(437) (((float\$4 adj (gate electrode plate trap\$4) FG) charge adj storage D) near4 (fl

(0) (((float\$4 adj (gate electrode plate trap\$4) FG) charge adj storage D

(2) (((float\$4 adj (gate electrode plate trap\$4) FG) charge adj storage D

(2304) ((FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) adj

(583) ((FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) adj2

(354) ((FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) adj2

(0) (((FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) adj2 (c

(3) (((FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) adj2 (c

(115408) (control adj (gate electrode plate) CG)

(8) (((FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) adj2 (c

(83) (((FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) adj2

Browse Queue Clear

DBs: USPAT:US FGPUB:EPO JPO:DERWENT:IBM:TDG

Default operator: OR

Plurals

+highlight all hit terms initially

((((FOX field adj oxide STI (isolati\$3 (element adj (insulat\$4 separat\$4)) adj2 (oxide region film structure) ) locos  
) near ((trench\$4 groove\$2)  
) same (((trench\$4 groove\$2)  
) near2 (width thick\$4)) and ((float\$4 adj (gate electrode plate trap\$4) FG) charge adj storage )  
)

July 2004

APA form APA form 23map RTed RTed

	U	I	Inv	Docu	Issue	P	Title	Current	Current	XR	Retrieval	S	C	P	2	3	4	5	6	7	8	9	10	Image	Doc	P
1							Dong, Cha De	US 2004012	20040	1	Method of manufacturing flash memory devi	438/259												US 200401	P	
2							Shimizu, Kaz	US 6555427	20030	5	Non-volatile semiconductor memory device a	438/238	257/314											US 655542	P	
3							Sumino, Jun	US 2004014	20040	3	Non-volatile semiconductor memory device a	257/315												US 200401	P	
4							Ogawa, Hisas	US 2004013	20040	2	Semiconductor device and its manufacturing	438/142												US 200401	P	
5							Tran, Luan C.	US 2004010	20040	1	6F2 DRAM array, a DRAM array formed on a	438/241	438/238											US 200401	P	
6							Harari, Eliyah	US 2004007	20040	2	FLASH MEMORY CELL ARRAYS HAVING DU	257/316												US 200400	P	
7							Lee, Peter W.	US 2004004	20040	3	Novel monolithic, combo nonvolatile memory	365/202	257/E21.68											US 200400	P	
8							Yoo, Tae-kwa	US 2004000	20040	9	Eaprom and method of fabricating the same	438/315	257/E21.87											US 200400	P	
9							Shimizu, Kaz	US 2003020	20031	5	Non-volatile semiconductor memory device a	438/424	257/E21.68											US 200302	P	
10							Shin, You-Ch	US 2003020	20031	9	Shallow trench isolation type semiconductor	257/501	257/E21.54											US 200302	P	

Ready